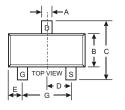
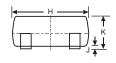
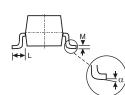


Features

- VDS=20V.
- Super high density cell design for extremely low RDS(ON).
- Exceptional on-resistance and maximum DC current capability.
- We declare that the material of product compliance with RoHS requirements.







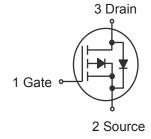
SOT-23						
Dim	Min	Max				
Α	0.37	0.51				
В	1.20	1.40				
С	2.30	2.50				
D	0.89	1.03				
Е	0.45	0.60				
G	1.78	2.05				
Н	2.80	3.00				
J	0.013	0.10				
K	0.903	1.10				
L	0.45	0.61				
M	0.085	0.180				
α	0°	8°				
All Dimensions in mm						

APPLICATIONS

- Power Management in Notebook.
- · Portable equipment.
- Battery powered system.
- Load switch.
- Marking Code:2301.

Maximum Ratings @ T_A = 25°C unless otherwise specified

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V_{DS}	-20	V	
Gate-Source Voltage	V _{GS}	± 8	V	
Drain Current	I _D	-2.8	А	
Peak Drain Current 1)	I _{DM}	-8	А	
Power Dissipation $T_A = 25^{\circ}C$ $T_A = 75^{\circ}C$	P _{tot}	0.9 0.57	W	
Thermal Resistance from Juntion to Ambient (PCB mounted) 2)	$R_{\theta JA}$	140	°C/W	
Junction Temperature	T _J	150	$^{\circ}$	
Storage Temperature Range	T _{stg}	- 55 to + 150	$^{\circ}$	



 $^{^{\}mbox{\scriptsize 1)}}\mbox{Repetitive Rating:}$ Pulse width limited by the Maximum junction temperation.

²⁾ 1 in² 2oz Cu PCB board.



Electrical Characteristics @ TA = 25°C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Static				'	•	•
Drain-source breakdown voltage	V(BR)DSS	V _G S = 0V, I _D =-250µA	-20			V
Gate-source threshold voltage	VGS(th)	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0	-1	
Gate-source leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±8V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μA
Drain-source on-state resistance ^a	RDS(on)	V _{GS} =-4.5V, I _D =-2.8A		0.090	0.112	Ω
		V _{GS} =-2.5V, I _D =-2.0A		0.110	0.142	
Forward transconductance ^a	g _{fs}	V _{DS} =-5V, I _D =-2.8A		6.5		S
Dynamic ^b		1		U.		ļ.
Input capacitance	C _{iss}	V _{DS} =-10V,V _{GS} =0V,f =1MHz		405		pF
Output capacitance	C _{oss}			75		
Reverse transfer capacitance	C _{rss}			55		
Total gata charge	Qg	V _{DS} =-10V,V _{GS} =-4.5V,I _D =-3A		5.5	10	nC
Total gate charge		V _{DS} =-10V,V _{GS} =-2.5V,I _D =-3A		3.3	6	
Gate-source charge	Q _{gs}			0.7		
Gate-drain charge	Q_{gd}			1.3		
Gate resistance	Rg	f=1MHz		6.0		Ω
Turn-on delay time	td(on)	V_{DD} =-10V, R_{L} =10 Ω , I_{D} =-1A, V_{GEN} =-4.5V, Rg =1 Ω		11	20	- ns
Rise time	tr			35	60	
Turn-off delay time	td(off)			30	50	
Fall time	t f			10	20	
Drain-source body diode characterist	ics		•	•		•
Continuous source-drain diode current	Is	T _C =25°C			-1.3	А
Pulse diode forward current ^a	I _{SM}				-10	1
Body diode voltage	V_{SD}	I _S =-0.7A		-0.8	-1.2	V

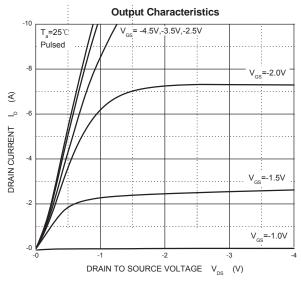
Notes:

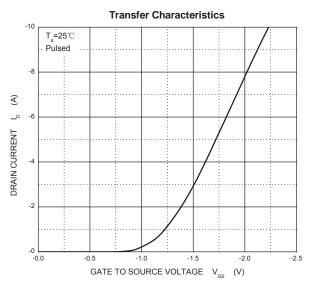
a.Pulse Test : Pulse Width < 300µs, Duty Cycle ≤2%.

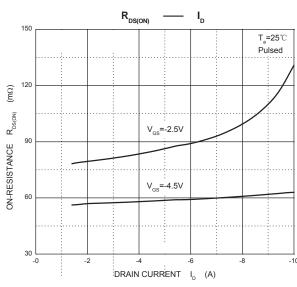
b.Guaranteed by design, not subject to production testing.

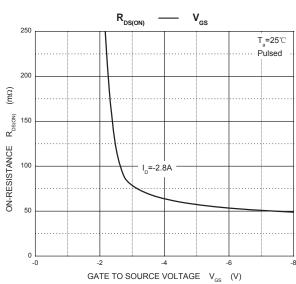


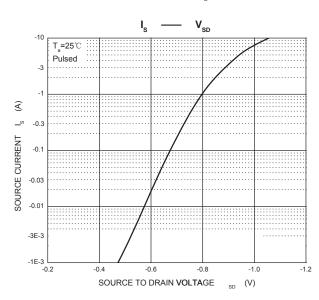
TYPICAL TRANSIENT CHARACTERISTICS













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